

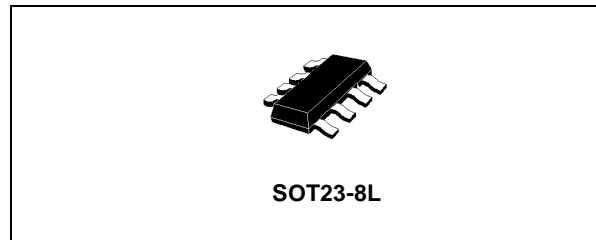
## DUAL BUS BUFFER (3-STATE)

- HIGH SPEED:  $t_{PD} = 3.8\text{ns}$  (TYP.) at  $V_{CC} = 5\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1\mu\text{A}$ (MAX.) at  $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS:  
 $V_{IH} = 2\text{V}$  (MIN),  $V_{IL} = 0.8\text{V}$  (MAX)
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 8\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:  
 $V_{CC}(\text{OPR}) = 4.5\text{V}$  to  $5.5\text{V}$
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74V2T125 is an advanced high-speed CMOS DUAL BUS BUFFER fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

3-STATE control input  $\overline{nG}$  has to be set HIGH to place the output into the high impedance state.



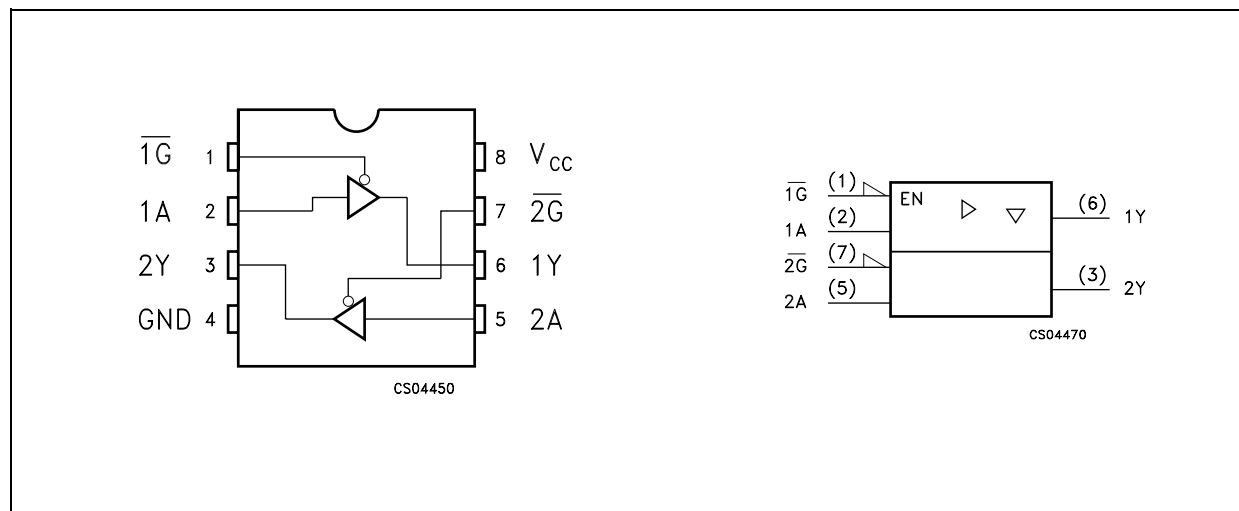
### ORDER CODES

PACKAGE	T & R
SOT23-8L	74V2T125STR

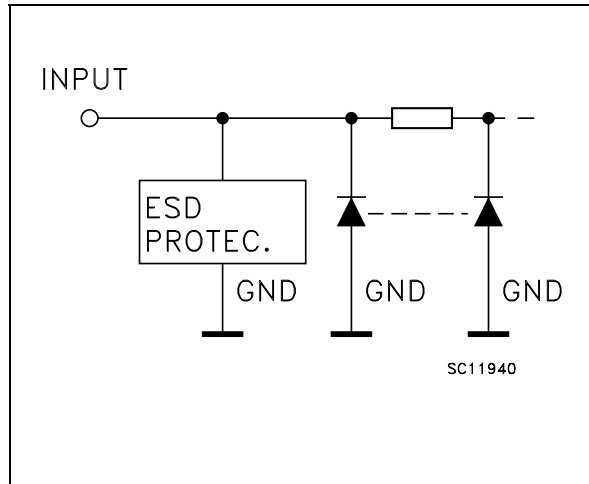
Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 3V to 5V systems and it is ideal for portable applications like personal digital assistant, camcorder and all battery-powered equipment.

All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



## INPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1, 7	$\overline{1G}, \overline{2G}$	Output Enable Inputs
2, 5	1A, 2A	Data Inputs
3, 6	2Y, 1Y	Data Outputs
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

## TRUTH TABLE

A	$\overline{G}$	Y
X	H	Z
L	L	L
H	L	H

X: "H" or "L"  
Z: High Impedance

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	- 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V <sub>CC</sub> = 5.0 ± 0.5V)	0 to 20	ns/V

1) V<sub>IN</sub> from 0.8V to 2V

## DC SPECIFICATION

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5		0.8			0.8		0.8		V
V <sub>IL</sub>	Low Level Input Voltage	4.5 to 5.5				2.0		2.0		2.0	V
V <sub>OH</sub>	High Level Output Voltage	4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
		4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		
V <sub>OL</sub>	Low Level Output Voltage	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = 5.5 or GND			±0.25		± 2.5		± 5	μA
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1		± 1	μA
I <sub>OPD</sub>	Power down Output Leakage Current	0	V <sub>O</sub> = 5.5			0.5		5		10	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			1		10		20	μA
ΔI <sub>CC</sub>	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5		1.5	mA

AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3ns)

Symbol	Parameter	Test Condition			Value						Unit	
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	5.0(*)	15			3.8	5.5	1.0	6.5	1.0	7.5	ns
		5.0(*)	50			4.3	6.5	1.0	7.5	1.0	8.5	
t <sub>PLZ</sub> t <sub>PHZ</sub>	Output Disable Time	5.0(*)	15	R <sub>L</sub> = 1 KΩ		3.6	5.0	1.0	6.0	1.0	7.0	
		5.0(*)	50	R <sub>L</sub> = 1 KΩ		5.1	7.0	1.0	8.0	1.0	9.0	
t <sub>PZL</sub> t <sub>PZH</sub>	Output Enable Time	5.0(*)	15	R <sub>L</sub> = 1 KΩ		3.7	5.9	1.0	7.0	1.0	8.0	
		5.0(*)	50	R <sub>L</sub> = 1 KΩ		4.1	6.5	1.0	7.5	1.0	8.5	

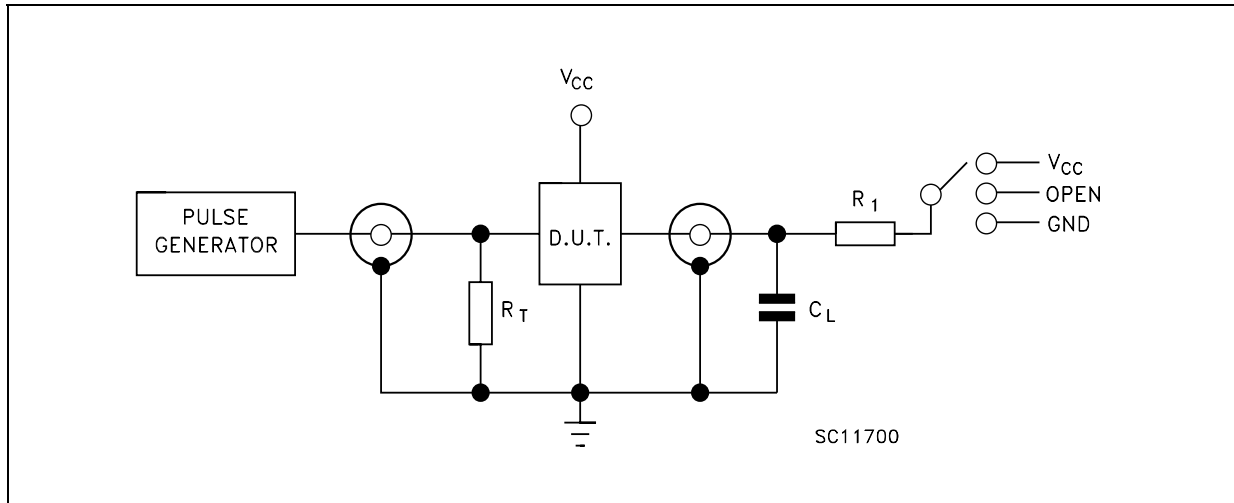
(\*) Voltage range is 5.0V ± 0.5V

**CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Test Condition	Value						Unit	
			T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
			Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C <sub>IN</sub>	Input Capacitance			4	10		10		10	pF
C <sub>OUT</sub>	Output Capacitance			6						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			14						pF

1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$

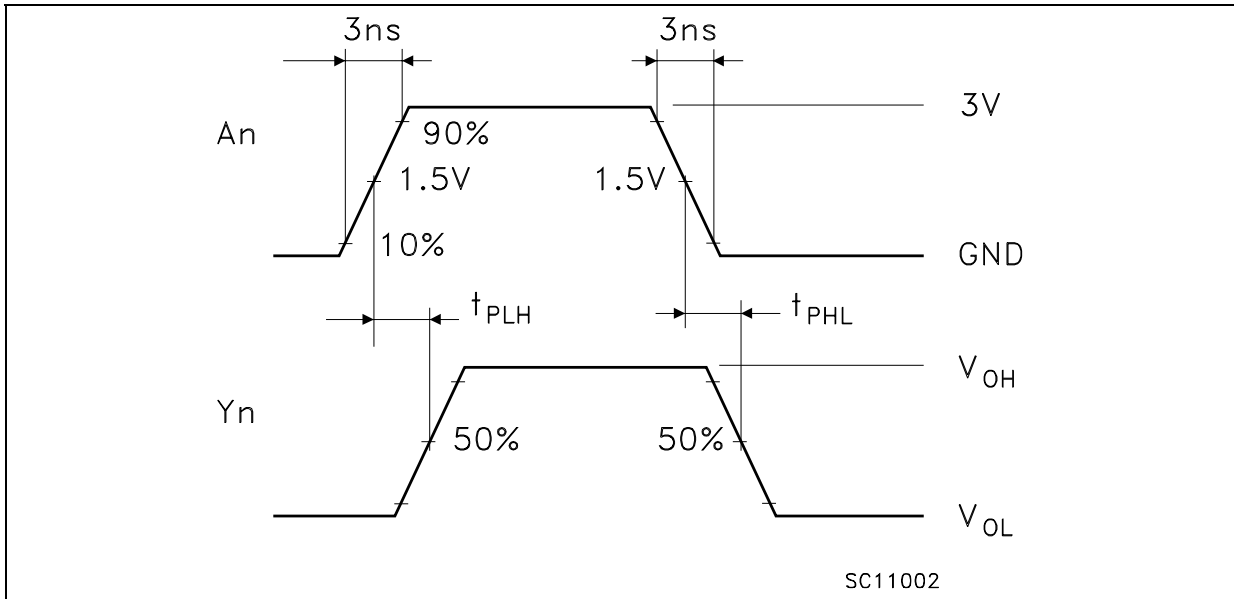
**TEST CIRCUIT TEST CIRCUIT**



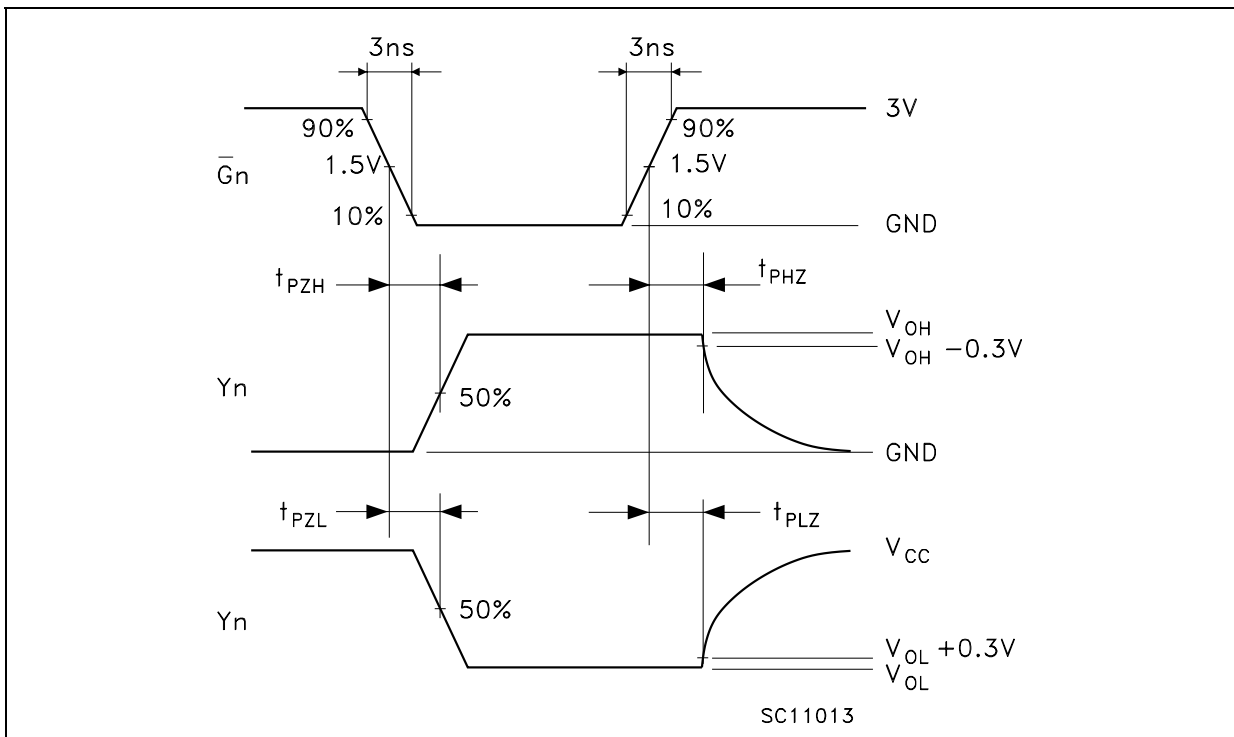
TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	V <sub>CC</sub>
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

C<sub>L</sub> = 15/50pF or equivalent (includes jig and probe capacitance)  
 R<sub>1</sub> = 1KΩ or equivalent  
 R<sub>T</sub> = Z<sub>OUT</sub> of pulse generator (typically 50Ω)

**WAVEFORM 1 : PROPAGATION DELAYS (f=1MHz; 50% duty cycle)**

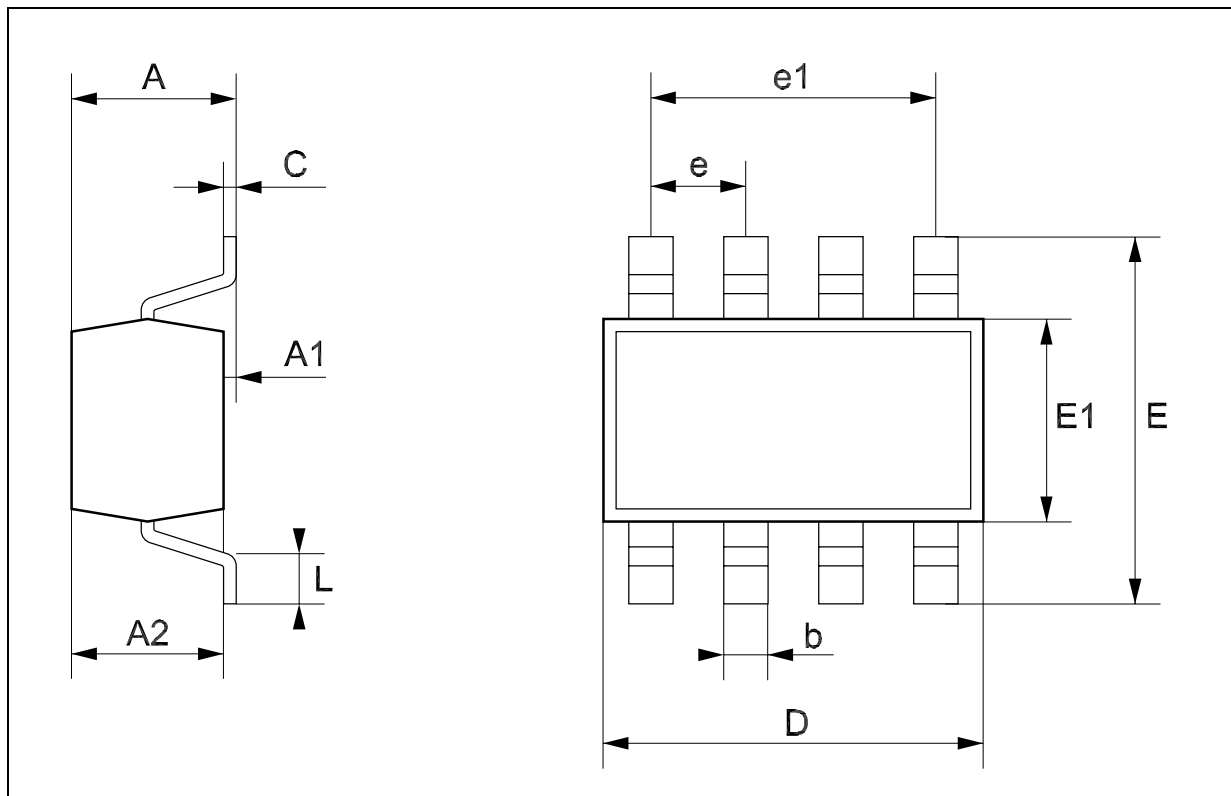


**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)**



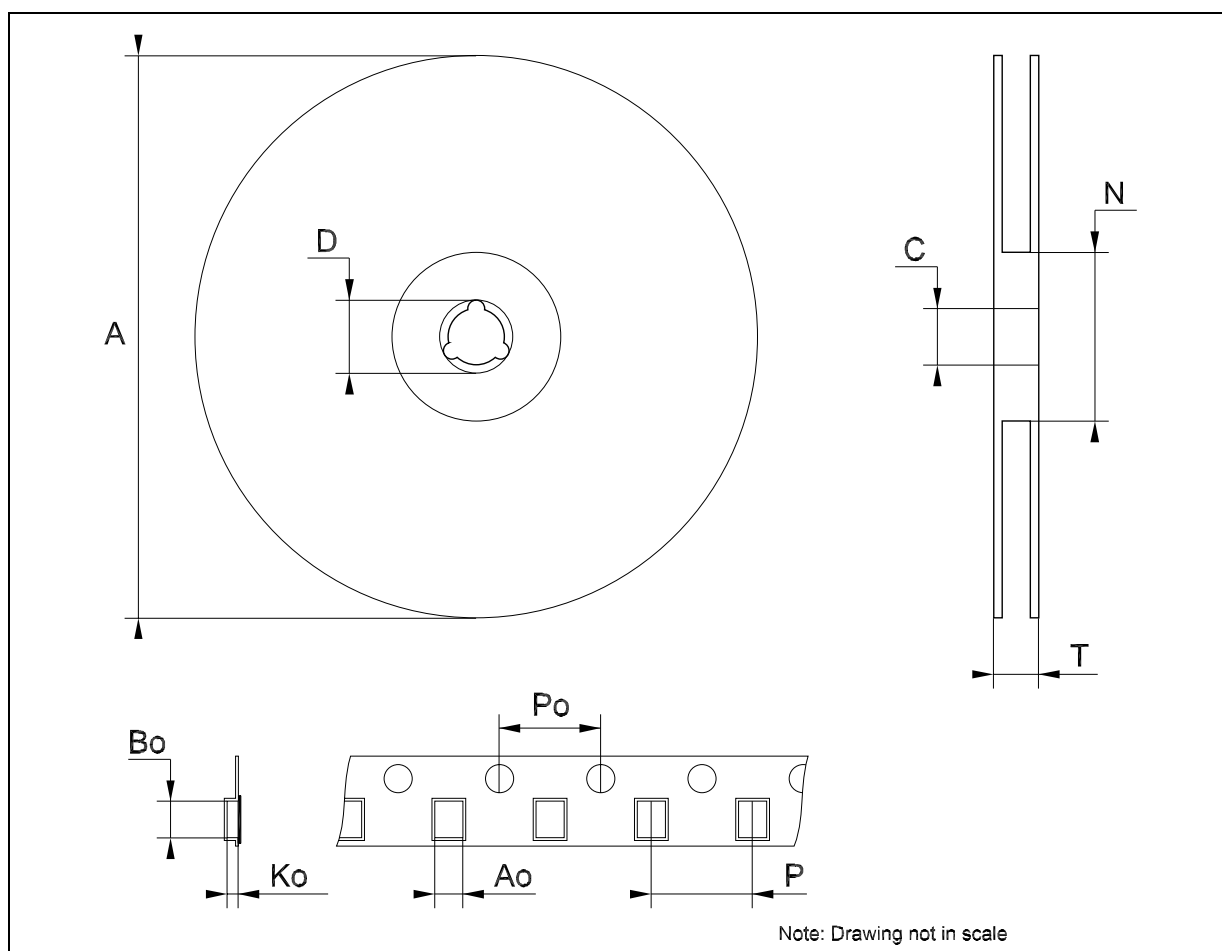
## SOT23-8L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6



## Tape &amp; Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157 <td 0.161	



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